



PTO/SB/08A (10-01)  
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Substitute for form 1449A/PTO		<b>Complete if Known</b>			
		Application Number	10/627,303		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Filing Date	7/24/03		
		First Named Inventor	Patel		
		Art Unit	Not Yet Assigned		
		Examiner Name	Not Yet Assigned		
Sheet	1	of	6	Attorney Docket Number	P109-US

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
BNT		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwaj, J.K.	
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		US- 2001/0002663 A1	06-07-2001	Tai et al.	
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		US- 2002/0185699	12-12-2002	Reid	
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		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
BUT		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwaj, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwaj, J.K.		
		WO-99/49506	09-30-1999	McQuarrie, A.D.		
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		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32163	07-23-1998	Tai et al.		

Examiner Signature	Brandi Thomas	Date Considered	7/29/04
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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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				Application Number	10/627,303
Sheet	2	of	6	Filing Date	7/24/03
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				Art Unit	Not Yet Assigned
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U.S. PATENT DOCUMENTS					
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		Number - Kind Code <sup>2</sup> (if known)			
BUT		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leuna, et al.	
		US- 6,238,581	05-29-2001	Hawkins, et al.	
		US- 6,115,172	09-05-2000	Jeong	
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		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
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FOREIGN PATENT DOCUMENTS						
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
BUT		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
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		JP-1986/61187238-A	08-20-1986	Nobuo et al.		
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		JP-1986/61181131-A	08-13-1986	Shinji et al.		

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		Application Number	10/627,303
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	P109-US
Sheet	4	of	6

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>2</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
BNT		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F <sub>2</sub> and XeF <sub>2</sub> Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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BUT		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
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		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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BNT		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF <sub>2</sub> Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
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		SUGANO et al., "Study on XeF <sub>2</sub> Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the MiteI 1.5- $\mu$ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
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		SEBEL et al., "Etching of Si Through a Thick Condensed XeF <sub>2</sub> Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sep/Oct 2000), pp. 2090-2097 (abstract only).	

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		APPLICANT Patel, et al.					
		FILING DATE 7/24/03		GROUP Not Yet Assigned			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
BNT	6,028,690	02/22/00	Carter, et al.	359	224		
FOREIGN PATENT DOCUMENTS							
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER	Brandi Thomas			DATE CONSIDERED		7/29/04	

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EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
BNT	6,522,454	02/18/03	Meier, et al.				
<b>FOREIGN PATENT DOCUMENTS</b>							
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						<input type="checkbox"/>	<input type="checkbox"/>
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
EXAMINER	<i>Brandt</i>			DATE CONSIDERED 7/29/04			

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